

Electronic Information Disclosure Statement

HIGH IMPEDANCE ANTIFUSE

3C474 U.S. PTO
10/064375
07/08/02

Application:

Confirmation:

Applicant(s): John Fifield

Docket Number: BUR920010181

Group Art Unit:

Examiner:

search string: (6240033 or 6140692 or 6051851 or 6020777 or 5909049 or 5557136 or 5242851 or re36893).pn.





#2 / IDS
8-2-02
R. Fisher

■ That each item of information contained in the information disclosure statement was cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Citation No.	Patent Number	Date	Bar Code	Patentee	Class	Subclass
ph	P01	6240033	2001-05-29		Yang et al.		
um	P02	6140692	2000-10-31		Sher et al.		
um	P03	6051851	2000-04-18		Ohmi et al.		
um	P04	6020777	2000-02-		Bracchitta et al.		

			01		
<i>m</i>	P05	5909049	1999-06-01		McCollum
<i>m</i>	P06	5557136	1996-09-17		Gordon et al.
<i>m</i>	P07	5242851	1993-09-07		Choi
<i>m</i>	P08	re36893	2000-10-03		Pramanik et al.

Remarks

(Remarks are not for responding to an office action.)

"Impact of Shallow Trench Isolation on Reliability of Buried-and Surface-Channel sub-um PFET" IEEE 1995, pages 24-29

Signature

Examiner Name	Date
<i>Kang, Dongha</i>	<i>4-23-03</i>